TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA75558P, TA75558S, TA75558F

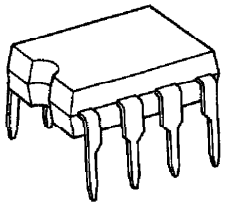
DUAL OPERATIONAL AMPLIFIER

The TA75558P, TA75558S and TA75558F are Low-Noise Operational Amplifiers with High Speed and Wide Bandwidth.

FEATURES

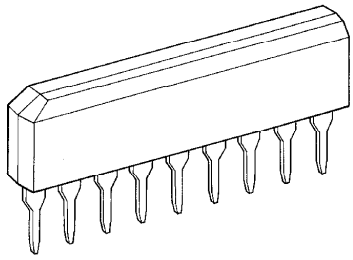
- Internal Frequency Compensation Type
- Pin Compatible with TA75458P, TA75458S and TA75458F
- Possible to Exchange the Position of 9 Pin for 1 Pin Because of Pin Connection Being Symmetric. (TA75558S Device Only)
- Wide Band Range : $f_T = 3MHz$ (Typ.)
- Suitable Application for Active Filter Equalizer Amplifier and Headphone Amplifier.

TA75558P



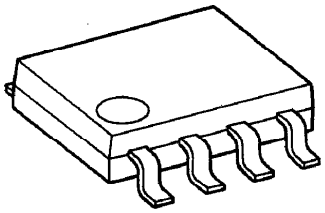
DIP8-P-300-2.54A

TA75558S



SIP9-P-2.54A

TA75558F



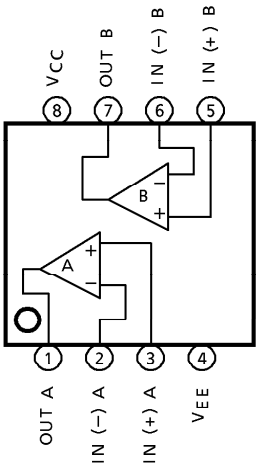
SOP8-P-225-1.27

Weight
DIP8-P-300-2.54A : 0.5g (Typ.)
SIP9-P-2.54A : 0.9g (Typ.)
SOP8-P-225-1.27 : 0.1g (Typ.)

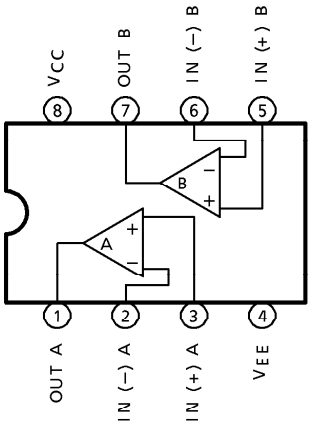
961001EBA1

PIN CONNECTION (TOP VIEW)

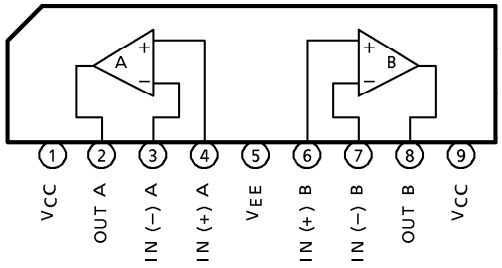
TA75558F



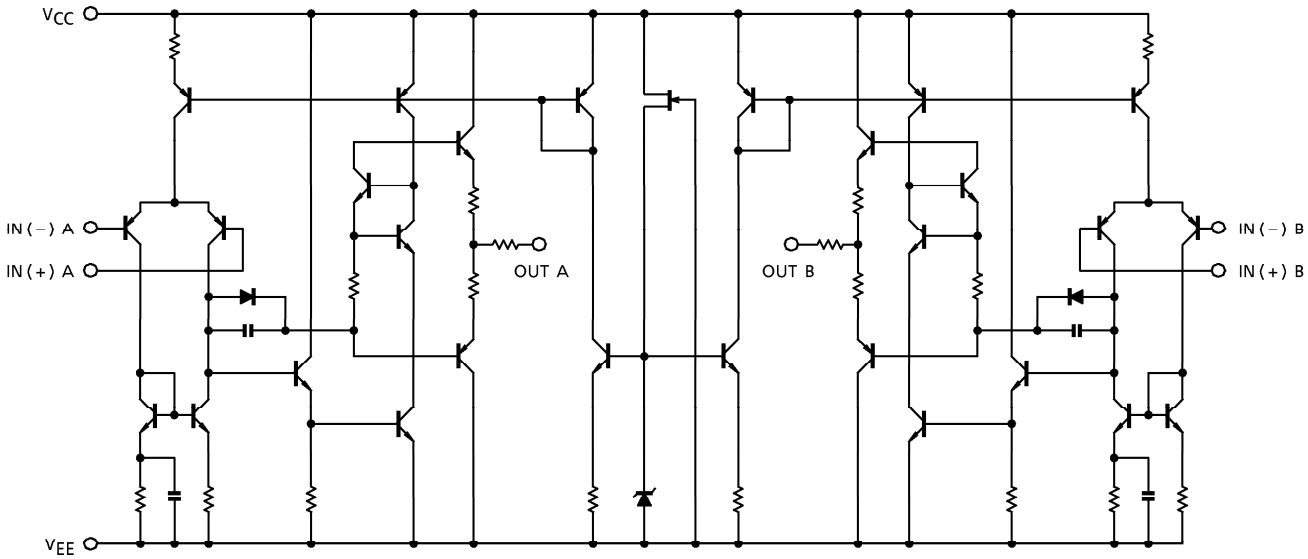
TA75558P



TA75558S



EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta = 25°C)

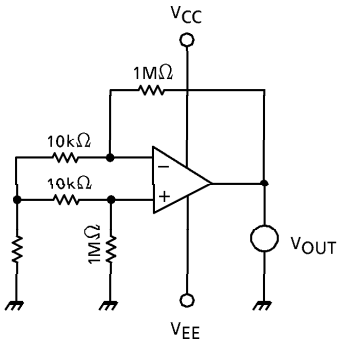
CHARACTERISTIC	SYMBOL	TA75558P TA75558S	TA75558F	UNIT
Supply Voltage	V_{CC}	+ 18	+ 18	V
	V_{EE}	− 18	− 18	
Differential Input Voltage	DV_{IN}	± 30	± 30	V
Input Voltage	V_{IN}	V_{CC}~V_{EE}	V_{CC}~V_{EE}	V
Power Dissipation	P_D	500	240	mW
Operating Temperature	T_{opr}	− 40~85	− 30~70	°C
Storage Temperature	T_{stg}	− 55~125	− 55~125	°C

ELECTRICAL CHARACTERISTICS (V_{CC} = 15V、V_{EE} = − 15V、Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	V_{IO}	1	$R_g \leqq 10k\Omega$	—	0.5	6	mV
Input Offset Current	I_{IO}	2	—	—	5	200	nA
Input Bias Current	I_I	2	—	—	60	500	nA
Common Mode Input Voltage	CMV_{IN}	3	—	± 12	± 14	—	V
Maximum Output Voltage	V_{OM}	6	$R_L = 10k\Omega$	± 12	± 14	—	V
	V_{OMR}		$R_L = 2k\Omega$	± 10	± 13	—	
Source Current	I_{source}	8	—	—	40	—	mA
Sink Current	I_{sink}	7	—	—	40	—	mA
Voltage Gain (Open Loop)	G_V	5	V_{OUT} = ± 10V, $R_L = 2k\Omega$	86	100	—	dB
Common Mode Input Signal Rejection Ratio	CMRR	3	$R_g \leqq 10k\Omega$	70	90	—	dB
Supply Voltage Rejection Ratio	SVRR	1	$R_g \leqq 10k\Omega$	—	30	150	μV / V
Slew Rate	SR	9	G_V = 1, $R_L = 2k\Omega$	—	1.0	—	V / μs
Unity Gain Cross Frequency	f_T	5	Open Loop	—	3.0	—	MHz
Supply Current	I_{CC}, I_{EE}	4	—	—	4.0	6.0	mA
Equivalent Input Noise Voltage	V_{NI}	—	R_S = 1kΩ, f = 30Hz~30kHz	—	2.5	—	μV_{rms}

TEST CIRCUIT

(1) V_{IO}, S_{VRR}

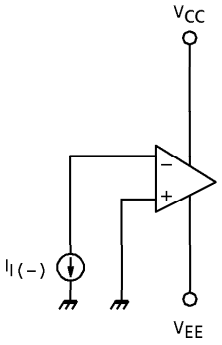


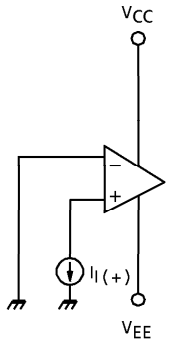
- $V_{IO} = V_{OUT} / 100$
- SVRR = 20ℓog E (dB)

$$E = \left| \frac{V_{OUT1} - V_{OUT2}}{(V_{CC1} - V_{EE1}) - (V_{CC2} - V_{EE2})} \right| \times \frac{1}{100}$$

V_{OUT1} : V_{OUT} (V_{CC}, V_{EE} = ± 8V)
V_{OUT2} : V_{OUT} (V_{CC}, V_{EE} = ± 18V)
V_{CC1} : V_{CC} = − 8V
V_{EE1} : V_{EE} = − 8V
V_{CC2} : V_{CC} = + 18V
V_{EE2} : V_{EE} = − 18V

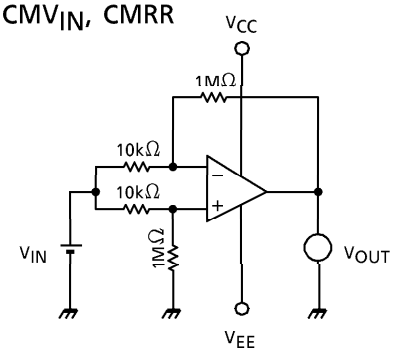
(2) I_I, I_{IO}





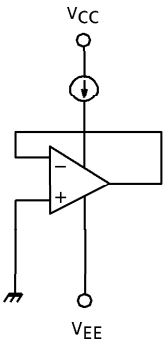
$I_{IO} = |I_I(-) - I_I(+)|$

(3) CMV_{IN}, CMRR



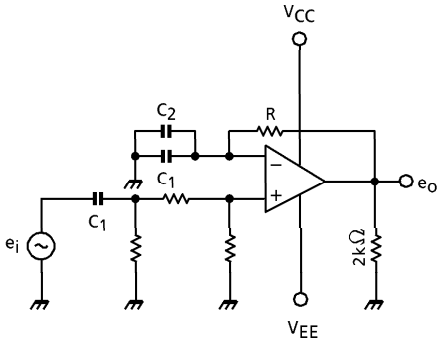
- CMRR = 20ℓog G_D / G_C (dB)
  G_D : DIFFERENTIAL VOLTAGE GAIN
  G_C : COMMON MODE VOLTAGE GAIN
- CMV_{IN} : V_{IN} = − 12V, 12V SUPPLIES

(4) I_{CC}



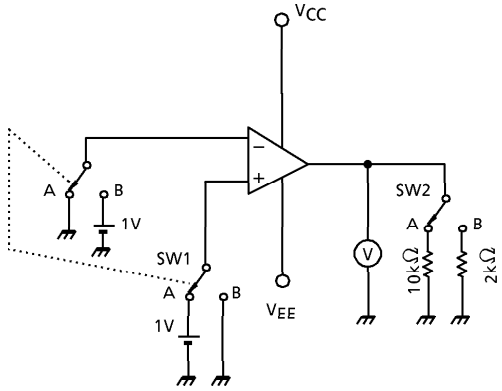
- I_{CC} : V_{CC}, $V_{EE} = \pm 15V$

(5) G_V, f_T



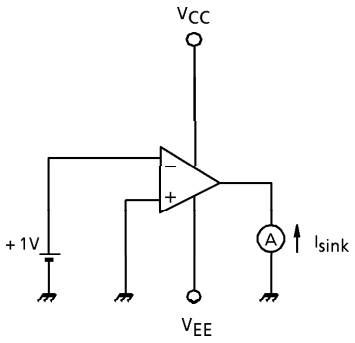
- $G_V = 20\ell og\ e_o / e_i$ (dB)
  $R \gg 1 / W_{C1}$
  C_1 : COUPLING CONDENSER
  C_2 : HIGH FREQUENCY BYPASS CONDENSER
- f_T : INPUT FREQUENCY AT $e_i = e_o$

(6) V_{OM}, V_{OMR}

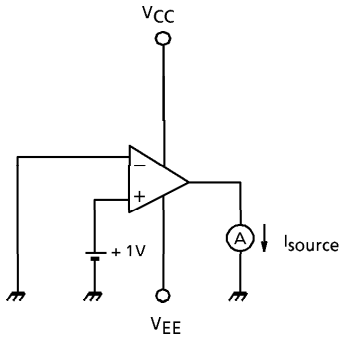


- V_{OM} : (+) : SW1 IS SIDE A, SW2 IS SIDE A
  (−) : SW1 IS SIDE B, SW2 IS SIDE A
- V_{OMR} : (+) : SW1 IS SIDE A, SW2 IS SIDE B
  (−) : SW1 IS SIDE B, SW2 IS SIDE B

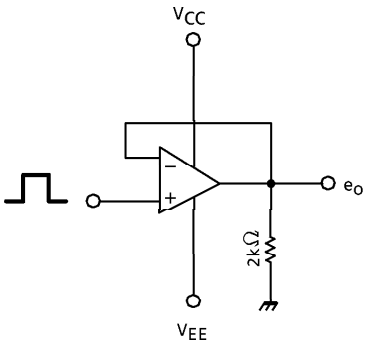
(7) I_{sink}

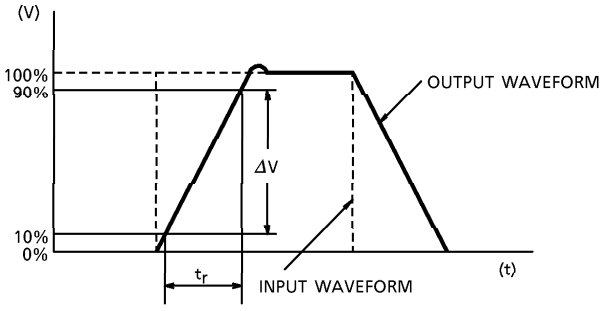


(8) I_{source}



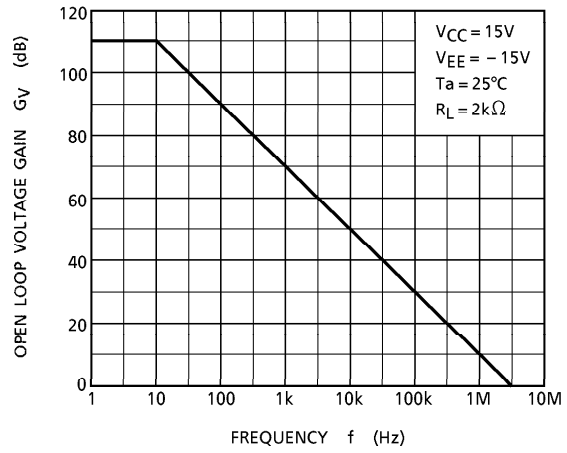
(9) SR



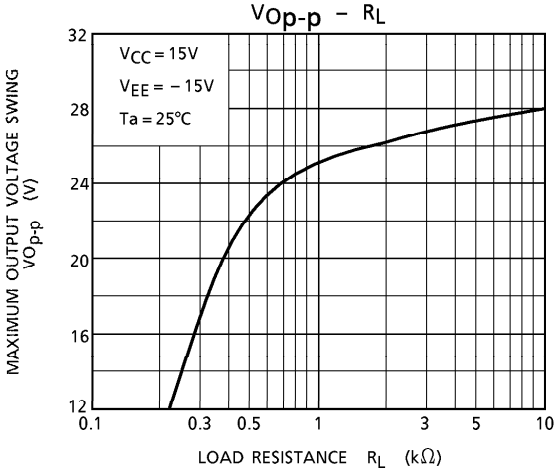


CHARACTERISTIC

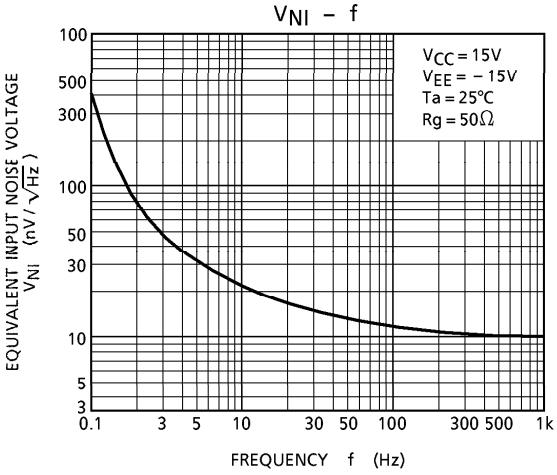
G_V – f



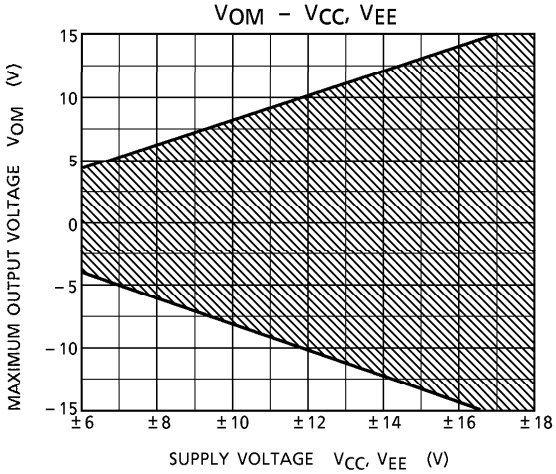
$V_{Op\text{-}p}$ – R_L



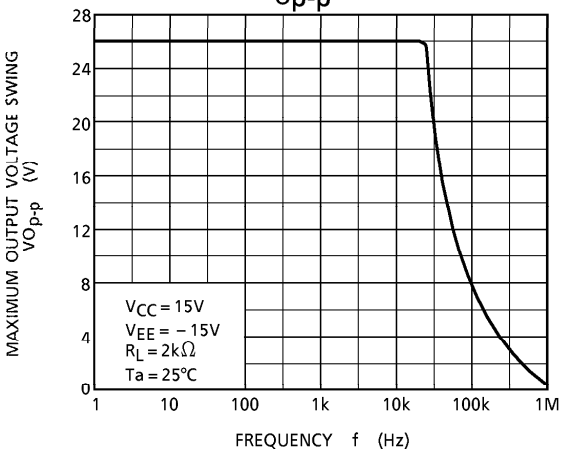
V_{NI} – f



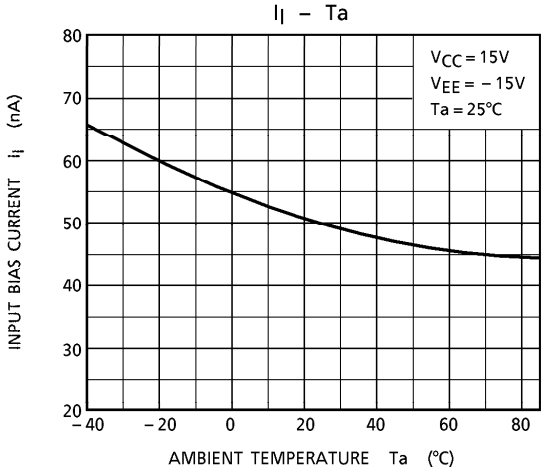
V_{OM} – V_{CC}, V_{EE}

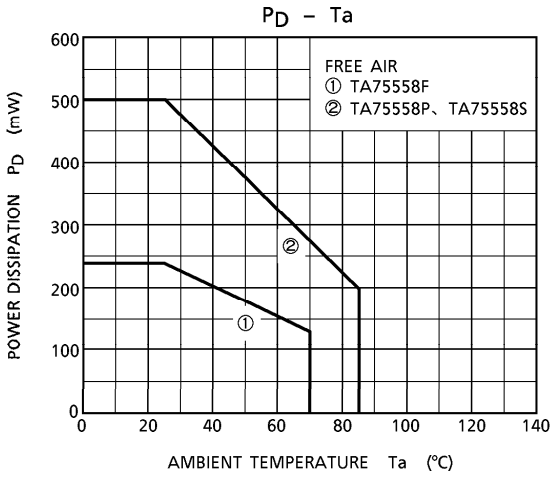


$V_{Op\text{-}p}$ – f



I_I – Ta

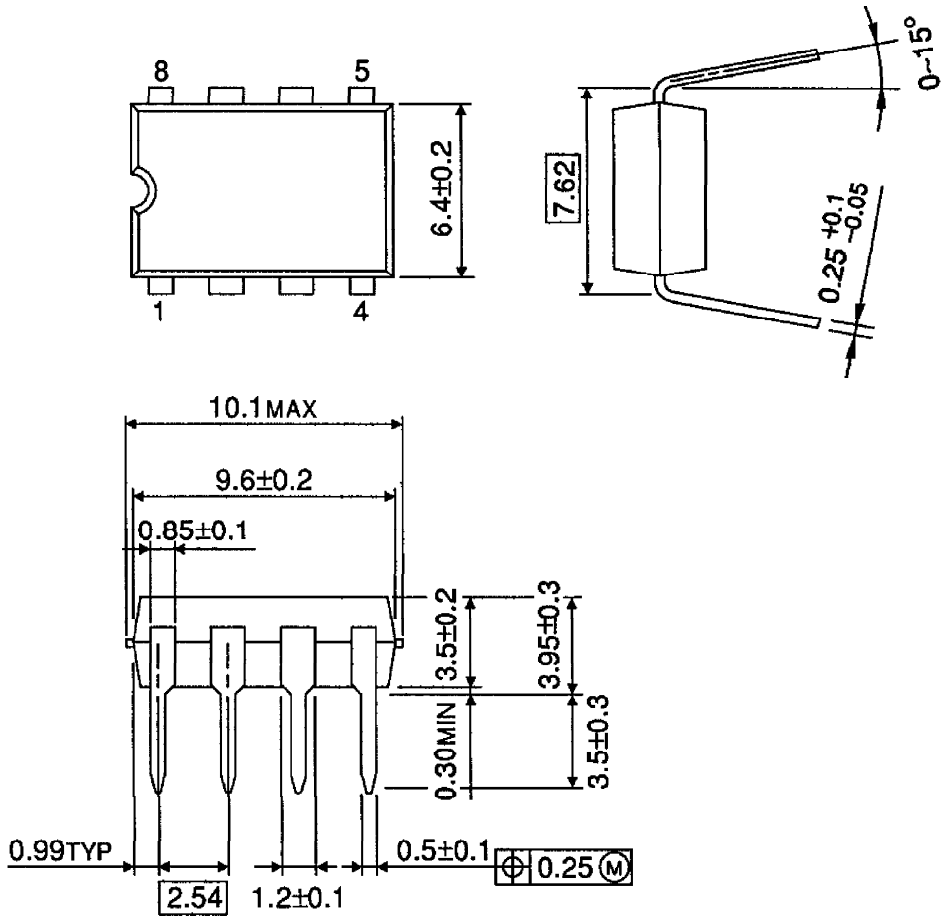




OUTLINE DRAWING

DIP8-P-300-2.54A

Unit : mm

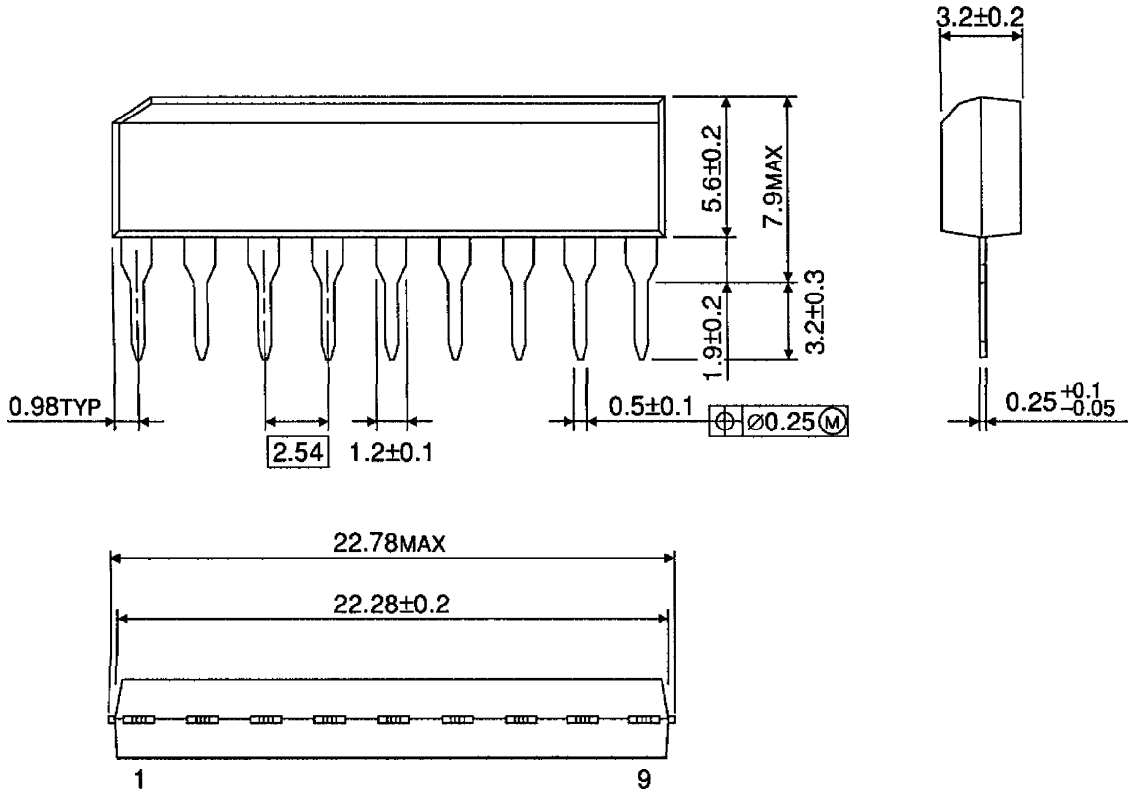


Weight : 0.5g (Typ.)

OUTLINE DRAWING

SIP9-P-2.54A

Unit : mm

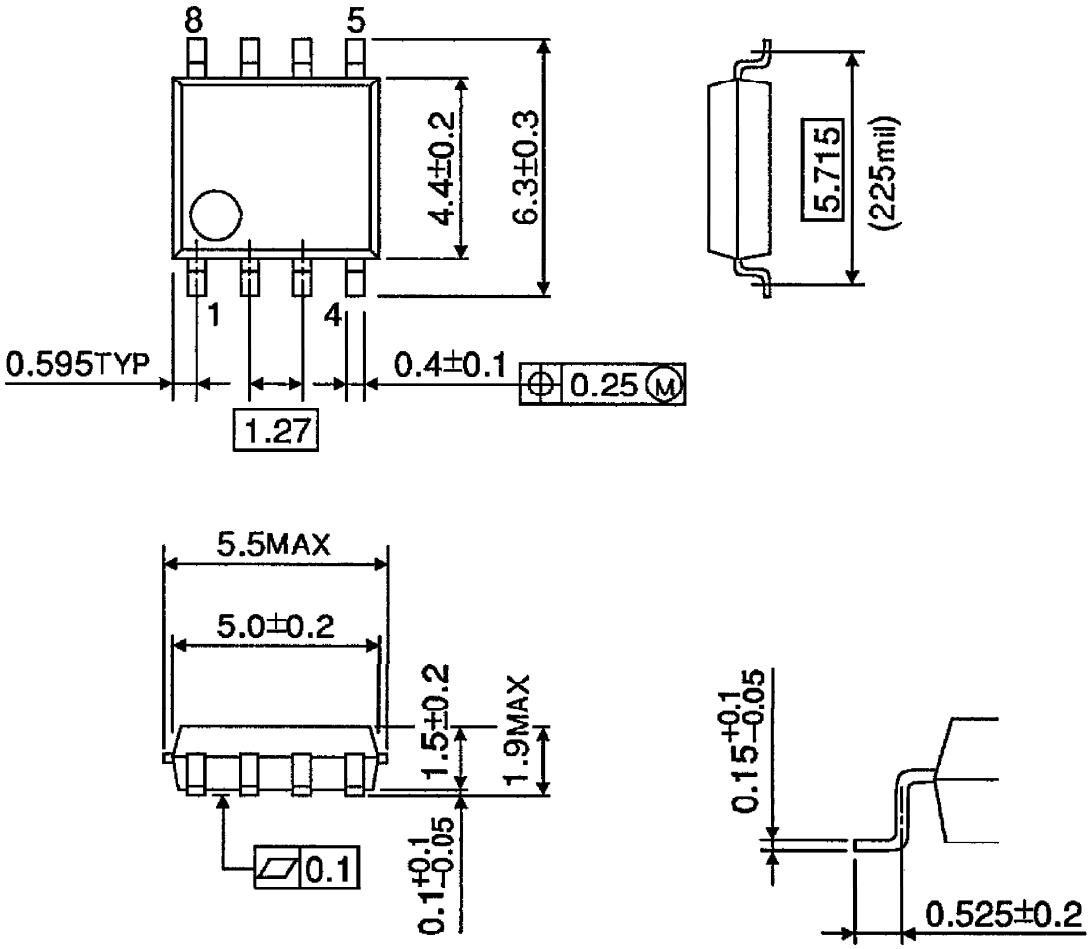


Weight : 0.9g (Typ.)

OUTLINE DRAWING

SOP8-P-225-1.27

Unit : mm



Weight : 0.1g (Typ.)